



**Shantou Huashan Electronic Devices Co.,Ltd.**

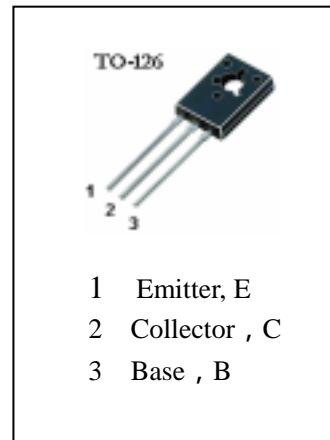
PNP SILICON TRANSISTOR OR  
**HSBD238**

## APPLICATIONS

Medium Power Linear switching Applications

## ABSOLUTE MAXIMUM RATINGS ( $T_a=25^\circ C$ )

$T_{stg}$ —Storage Temperature.....	-55~150
$T_j$ —Junction Temperature.....	150
$P_c$ —Collector Dissipation ( $T_c=25^\circ C$ ) .....	25W
$V_{CBO}$ —Collector-Base Voltage.....	100V
$V_{CEO}$ —Collector-Emitter Voltage.....	-80V
$V_{CER}$ —Collector-Emitter Voltage.....	-100V
$V_{EBO}$ —Emitter-Base Voltage.....	-5V
$I_c$ —Collector Current( Pulse ).....	-6A
$I_c$ —Collector Current ( DC ) .....	-2A



## ELECTRICAL CHARACTERISTICS ( $T_a=25^\circ C$ )

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
$I_{CBO}$	Collector Cut-off Current			-100	$\mu A$	$V_{CB}=-100V, I_E=0$
$I_{EBO}$	Emitter-Base Cut-off Current			-1	mA	$V_{EB}=-5V, I_C=0$
$h_{FE(1)}$	DC Current Gain	40				$V_{CE}=-2V, I_C=-150mA$
* $h_{FE(2)}$		25				$V_{CE}=-2V, I_C=-1A$
* $V_{CE(sat)}$	Collector-Emitter Saturation Voltage			-0. 6	V	$I_C=-1A, I_B=-0. 1A$
* $V_{BE(ON)}$	Base-Emitter On Voltage			-1. 3	V	$I_C=-1A, V_{CE}=-2V$
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	-80				$I_C=-100mA, I_B=0$
fT	Current Gain-Bandwidth Product	3			MHz	$I_C=-250mA, V_{CE}=-10V$

\* Pulse Test: PW=350  $\mu s$ , Duty Cycle 1. 5% Pulsed



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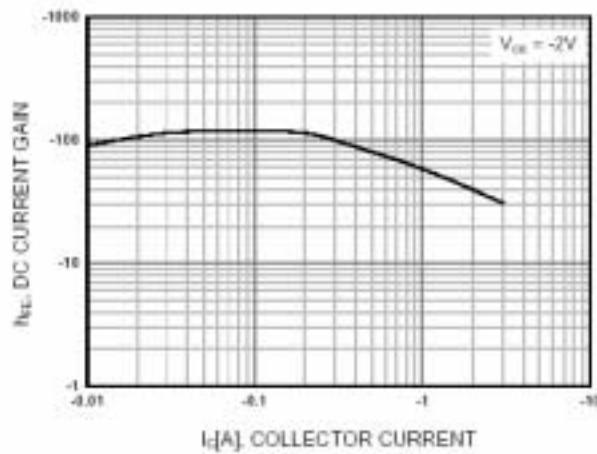


Figure 1. DC current Gain

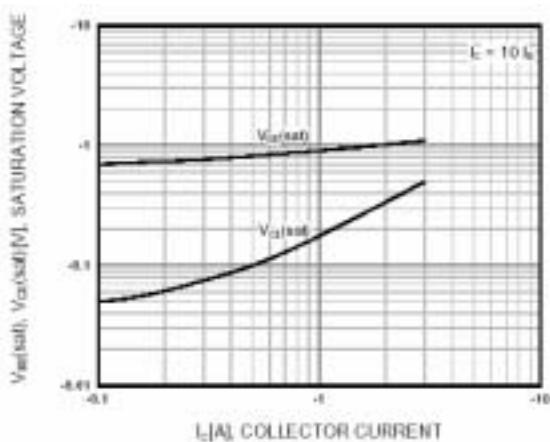


Figure 2. Base-Emitter Saturation Voltage  
Collector-Emitter Saturation Voltage

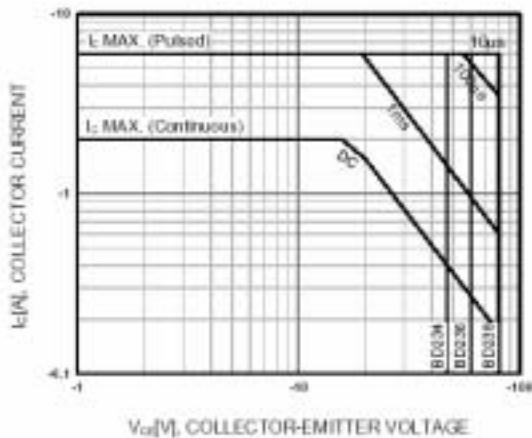


Figure 3. Safe Operating Area

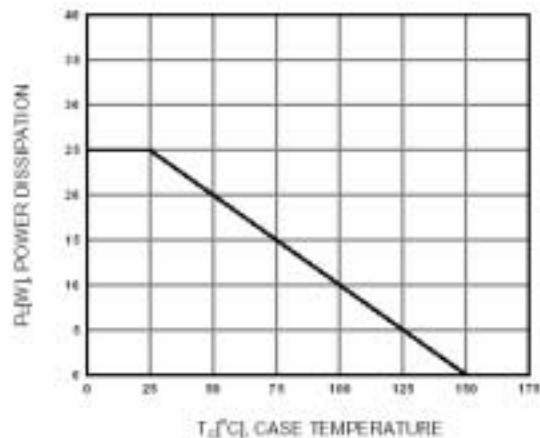


Figure 4. Power Derating